

FDP045N10A / FDI045N10A

MOSFET – N-Channel, POWERTRENCH®

100 V, 164 A, 4.5 mΩ

Description

This N-Channel MOSFET is produced using ON Semiconductor's advance POWERTRENCH process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Features

- $R_{DS(on)} = 3.8 \text{ m}\Omega$ (Typ.) @ $V_{GS} = 10 \text{ V}$, $I_D = 100 \text{ A}$
- Fast Switching Speed
- Low Gate Charge, $Q_G = 54 \text{ nC}$ (Typ.)
- High Performance Trench Technology for Extremely Low $R_{DS(on)}$
- High Power and Current Handling Capability
- This Device is Pb-Free and is RoHS Compliant

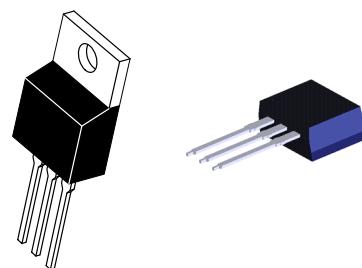
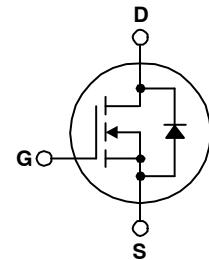
Applications

- Synchronous Rectification for ATX / Server / Telecom PSU
- Battery Protection Circuit
- Motor Drives and Uninterruptible Power Supplies
- Micro Solar Inverter



ON Semiconductor®

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TO-220
CASE 221A-09

I2PAK
CASE 418AV

MARKING DIAGRAM



\$Y = ON Semiconductor Logo
&Z = Assembly Plant Code
&3 = Numeric Date Code
&K = Lot Code
FDP/FDI045N10A = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

FDP045N10A / FDI045N10A

MOSFET MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter		FDP045N10A_F102 FDI045N10A_F102	Unit
V_{DSS}	Drain to Source Voltage		100	V
V_{GSS}	Gate to Source Voltage		± 20	V
I_D	Drain Current	– Continuous ($T_C = 25^\circ\text{C}$, Silicon Limited)	164*	A
		– Continuous ($T_C = 100^\circ\text{C}$, Silicon Limited)	116	
		– Continuous ($T_C = 25^\circ\text{C}$, Package Limited)	120	
I_{DM}	Drain Current	– Pulsed (Note 1)	656	A
E_{AS}	Single Pulsed Avalanche Energy (Note 2)		637	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		6.0	V/ns
P_D	Power Dissipation	($T_C = 25^\circ\text{C}$)	263	W
		– Derate Above 25°C	1.75	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range		–55 to +175	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

*Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 120 A.

THERMAL CHARACTERISTICS

Symbol	Parameter	FDP045N10A_F102 FDI045N10A_F102	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.57	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDP045N10A_F102	FDP045N10A	TO-220	Tube	N/A	N/A	50 Units
FDI045N10A_F102	FDI045N10A	I ² -PAK	Tube	N/A	N/A	50 Units

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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OFF CHARACTERISTICS

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \text{ mA}, V_{GS} = 0 \text{ V}$	100	–	–	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \text{ mA}$, Referenced to 25°C	–	0.07	–	$^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$	–	–	1	μA
		$V_{DS} = 80 \text{ V}, T_C = 150^\circ\text{C}$	–	–	500	
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	–	–	± 100	nA

ON CHARACTERISTICS

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \text{ mA}$	2.0	–	4.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 100 \text{ A}$	–	3.8	4.5	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS} = 10 \text{ V}, I_D = 100 \text{ A}$	–	132	–	S

FDP045N10A / FDI045N10A

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ Unless Otherwise Noted) (continued)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	$V_{DS} = 50\text{ V}$, $V_{GS} = 0\text{ V}$ $f = 1\text{ MHz}$	–	3960	5270	pF
C_{oss}	Output Capacitance		–	925	1230	pF
C_{rss}	Reverse Transfer Capacitance		–	34	–	pF
$C_{oss(er)}$	Energy Related Output Capacitance	$V_{DS} = 50\text{ V}$, $V_{GS} = 0\text{ V}$	–	1520	–	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{GS} = 10\text{ V}$, $V_{DS} = 50\text{ V}$, $I_D = 100\text{ A}$ (Note 4)	–	54	74	nC
Q_{gs}	Gate to Source Gate Charge		–	17	–	nC
Q_{gs2}	Gate Charge Threshold to Plateau		–	8	–	nC
Q_{gd}	Gate to Drain "Miller" Charge		–	13	–	nC
ESR	Equivalent Series Resistance (G-S)	$f = 1\text{ MHz}$	–	1.9	–	Ω

SWITCHING CHARACTERISTICS

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 50\text{ V}$, $I_D = 100\text{ A}$, $V_{GS} = 10\text{ V}$, $R_G = 4.7\text{ }\Omega$ (Note 4)	–	23	56	ns
t_r	Turn-On Rise Time		–	26	62	ns
$t_{d(off)}$	Turn-Off Delay Time		–	50	110	ns
t_f	Turn-Off Fall Time		–	15	40	ns

DRAIN-SOURCE DIODE CHARACTERISTICS

I_S	Maximum Continuous Drain to Source Diode Forward Current	–	–	164*	A	
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current	–	–	656	A	
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0\text{ V}$, $I_{SD} = 100\text{ A}$	–	–	1.3	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}$, $V_{DD} = 50\text{ V}$, $I_{SD} = 100\text{ A}$, $dI_F/dt = 100\text{ A/ms}$	–	75	–	ns
Q_{rr}	Reverse Recovery Charge		–	120	–	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. $L = 3\text{ mH}$, $I_{AS} = 20.6\text{ A}$, $R_G = 25\text{ }\Omega$, starting $T_J = 25^\circ\text{C}$.
3. $I_{SD} \leq 100\text{ A}$, $dI/dt \leq 200\text{ A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, starting $T_J = 25^\circ\text{C}$.
4. Essentially independent of operating temperature typical characteristics.

TYPICAL PERFORMANCE CHARACTERISTICS

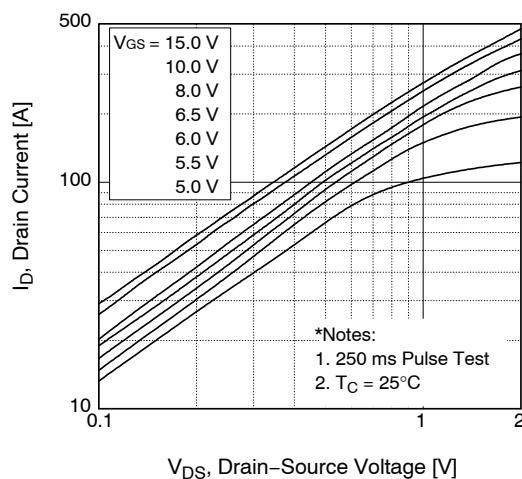


Figure 1. On-Region Characteristics

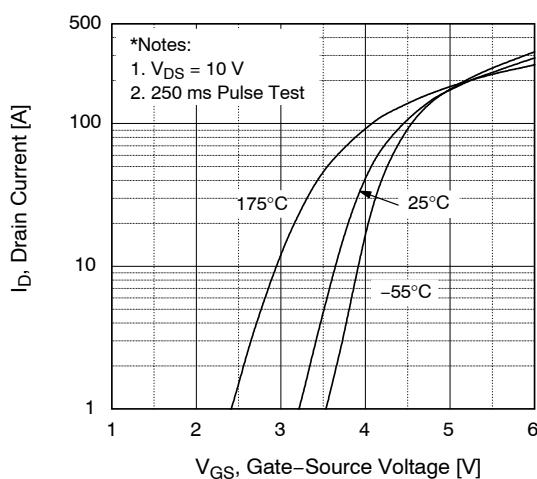


Figure 2. Transfer Characteristics

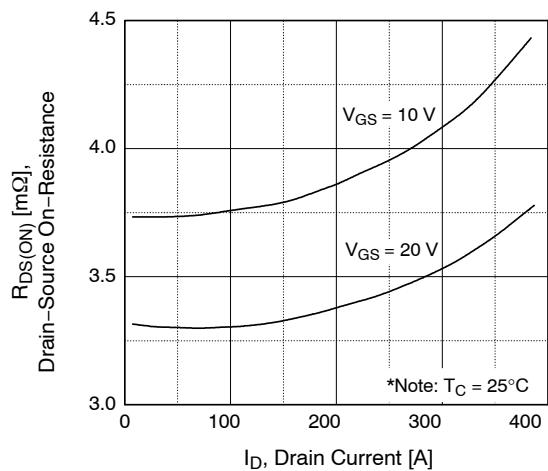


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

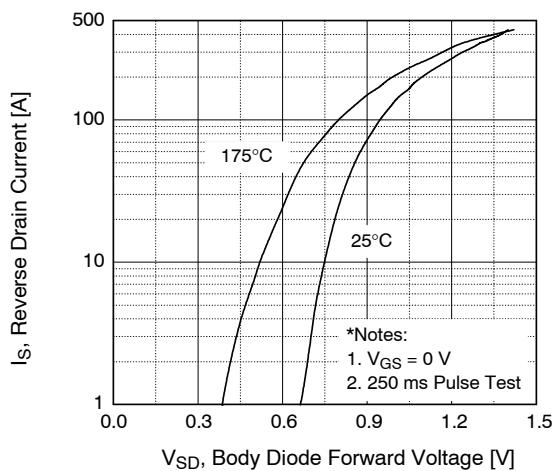


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

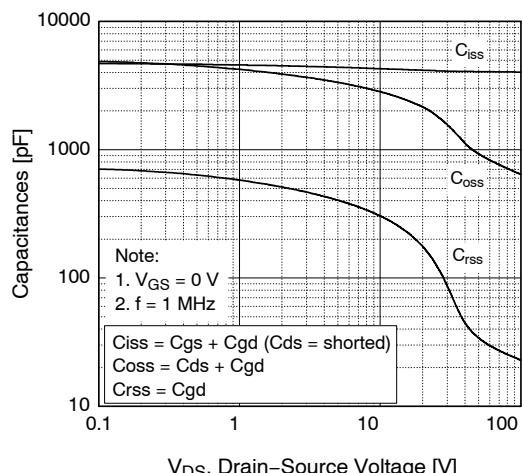


Figure 5. Capacitance Characteristics

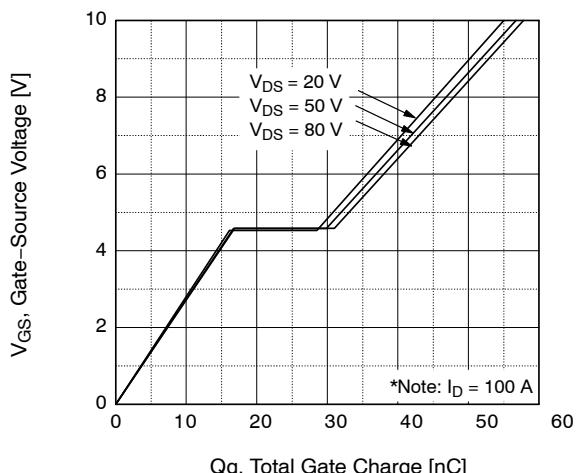
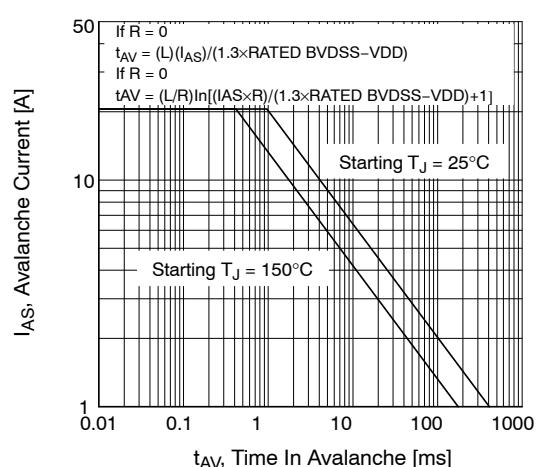
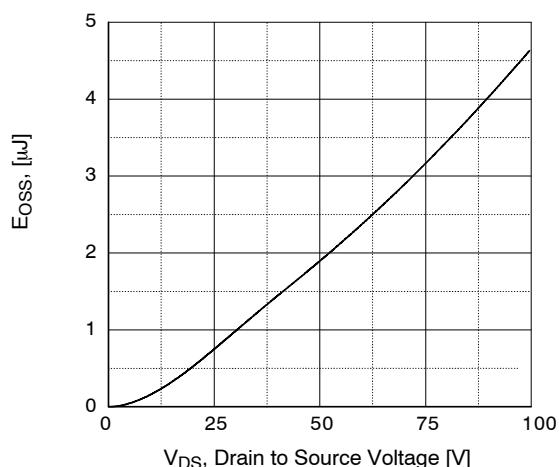
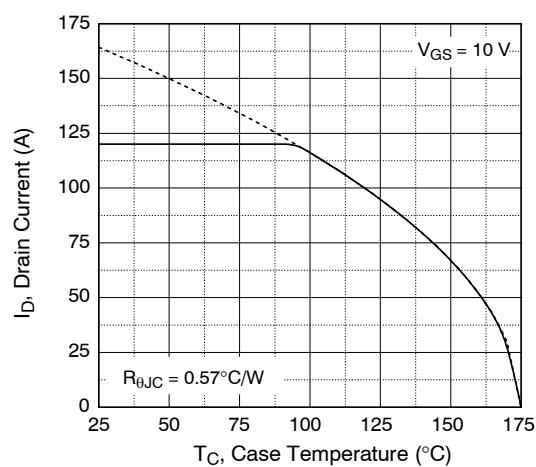
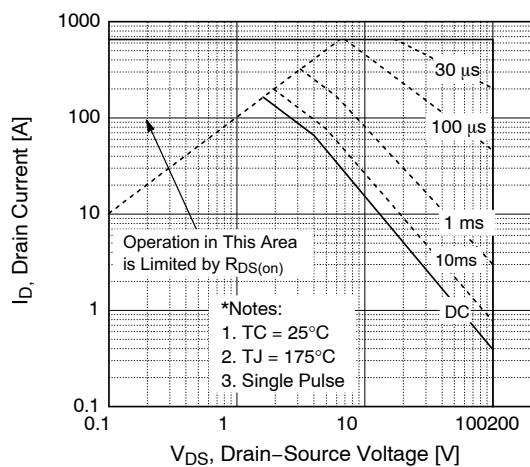
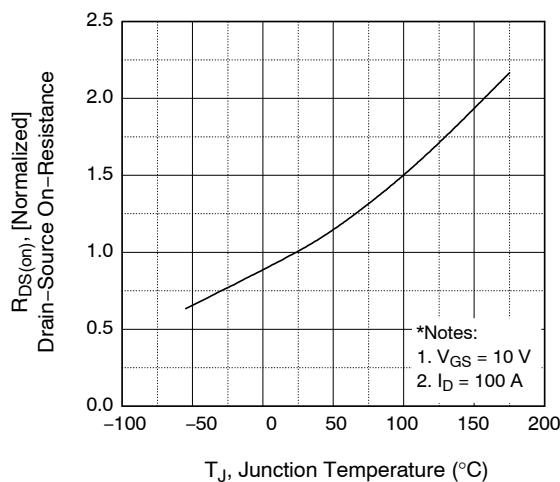
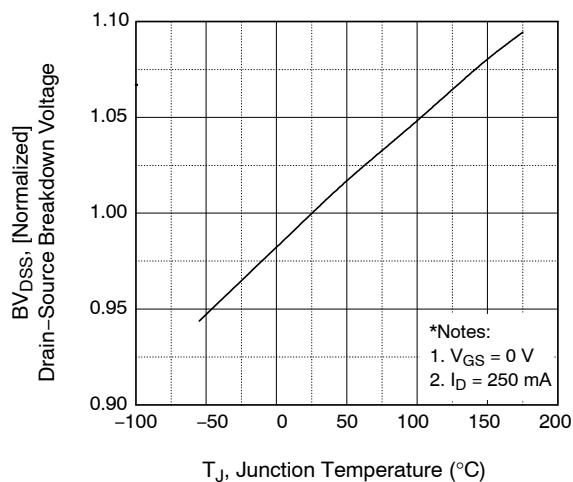


Figure 6. Gate Charge Characteristics

TYPICAL PERFORMANCE CHARACTERISTICS (continued)



TYPICAL PERFORMANCE CHARACTERISTICS (continued)

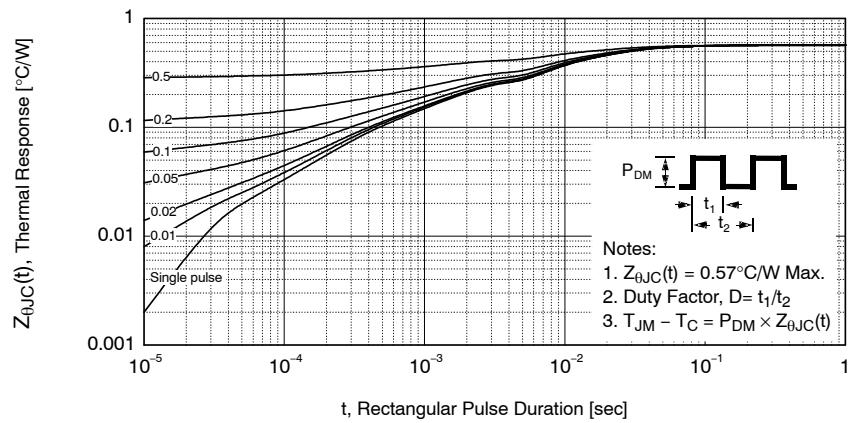


Figure 13. Transient Thermal Response Curve

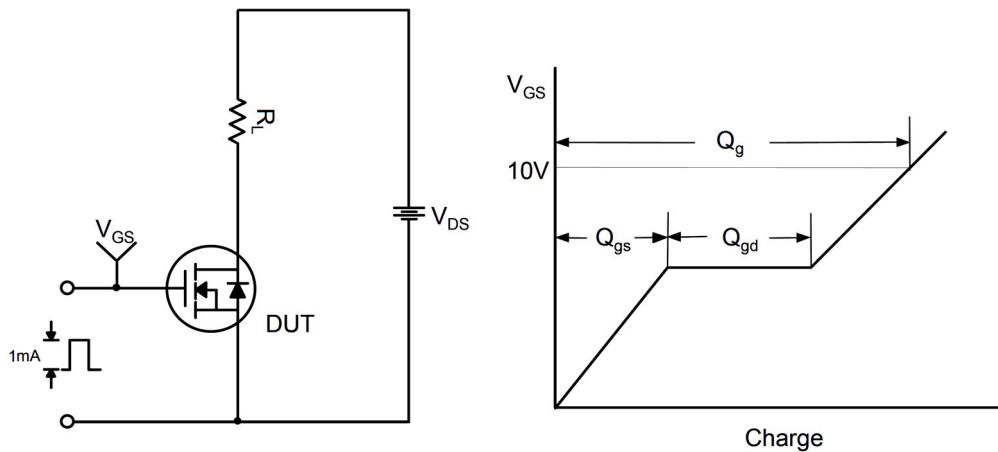


Figure 14. Gate Charge Test Circuit & Waveform

FDP045N10A / FDI045N10A

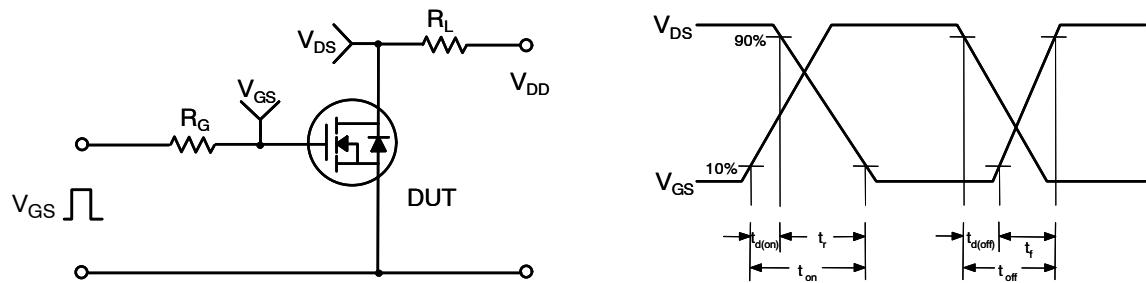


Figure 15. Resistive Switching Test Circuit & Waveforms

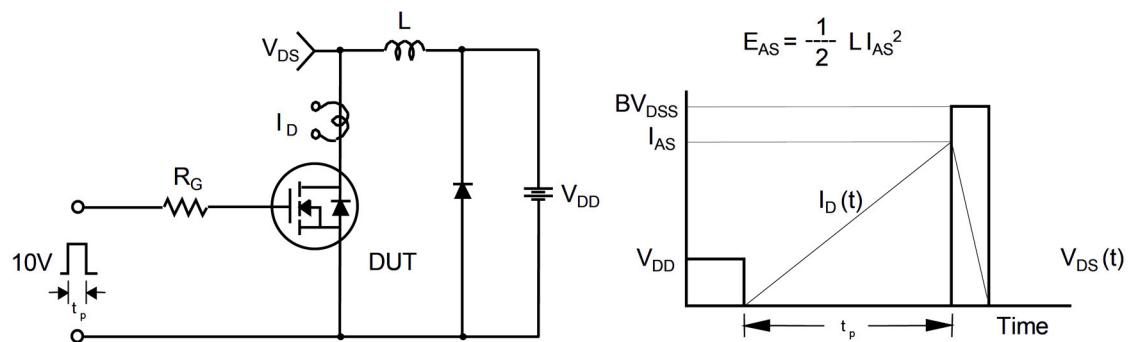


Figure 16. Unclamped Inductive Switching Test Circuit & Waveforms

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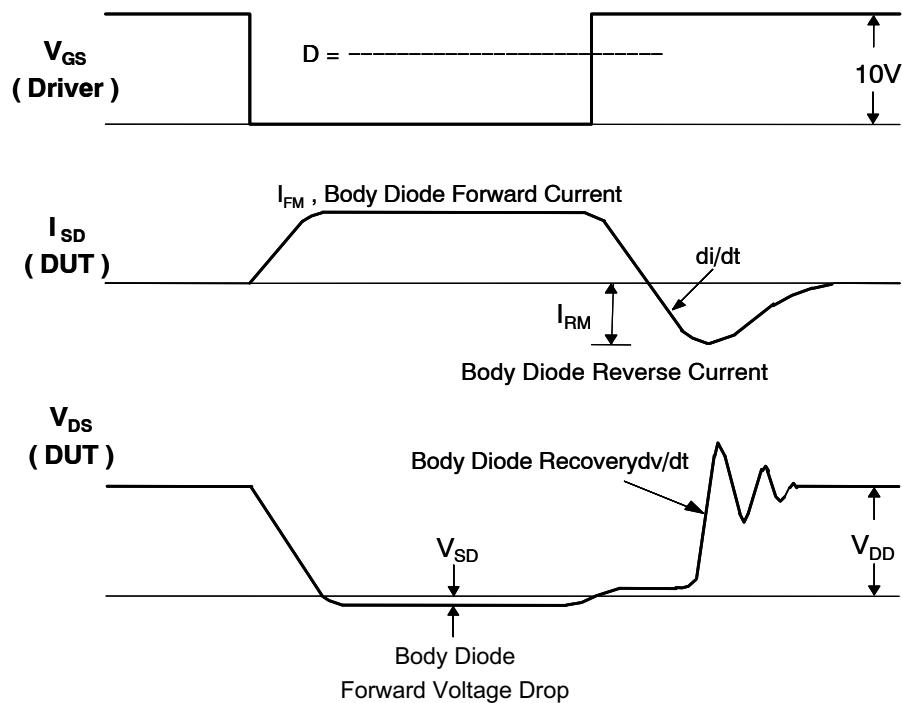
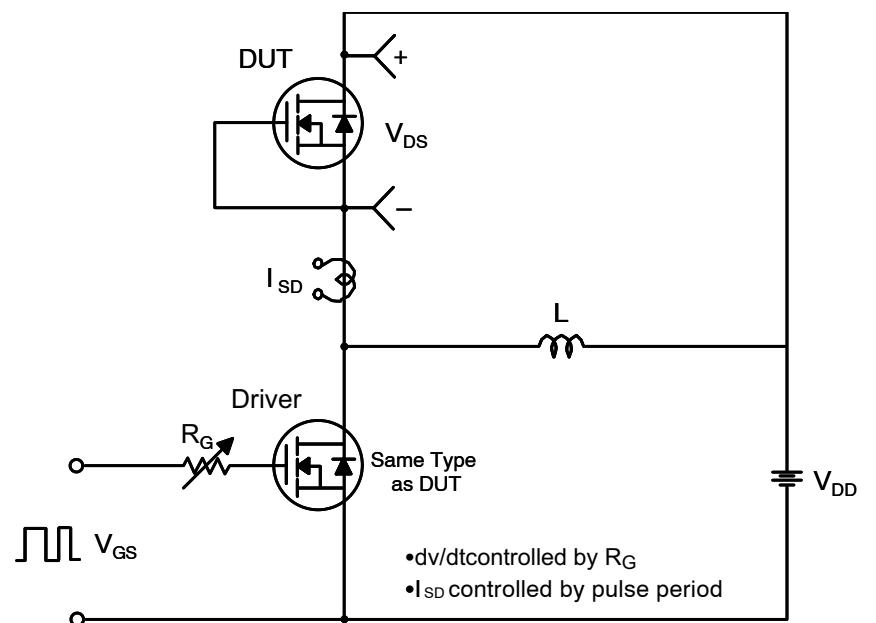


Figure 17. Peak Diode Recovery dv/dt Test Circuit & Waveforms

MECHANICAL CASE OUTLINE

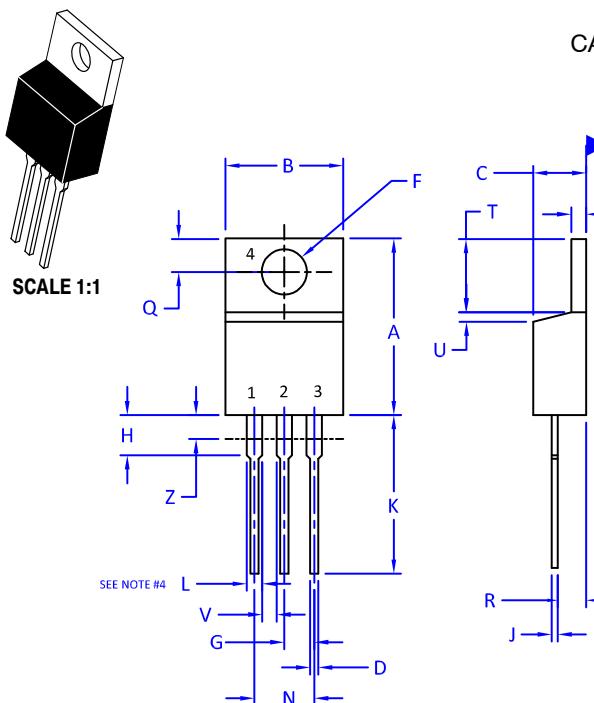
PACKAGE DIMENSIONS

ON Semiconductor®



TO-220 CASE 221A-09 ISSUE AJ

DATE 05 NOV 2019



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
2. CONTROLLING DIMENSION: INCHES
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.
4. MAX WIDTH FOR F102 DEVICE = 1.35MM

DIM	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.570	0.620	14.48	15.75
B	0.380	0.415	9.66	10.53
C	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.60	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.41
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	----	1.15	---
Z	----	0.080	---	2.04

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. Emitter
4. COLLECTOR

STYLE 5:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 9:
PIN 1. GATE
2. COLLECTOR
3. Emitter
4. COLLECTOR

STYLE 2:
PIN 1. BASE
2. Emitter
3. COLLECTOR
4. Emitter

STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

STYLE 10:
PIN 1. GATE
2. SOURCE
3. DRAIN
4. SOURCE

STYLE 3:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 7:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE

STYLE 11:
PIN 1. DRAIN
2. SOURCE
3. GATE
4. SOURCE

STYLE 4:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. MAIN TERMINAL 2

STYLE 8:
PIN 1. CATHODE
2. ANODE
3. EXTERNAL TRIP/DELAY
4. ANODE

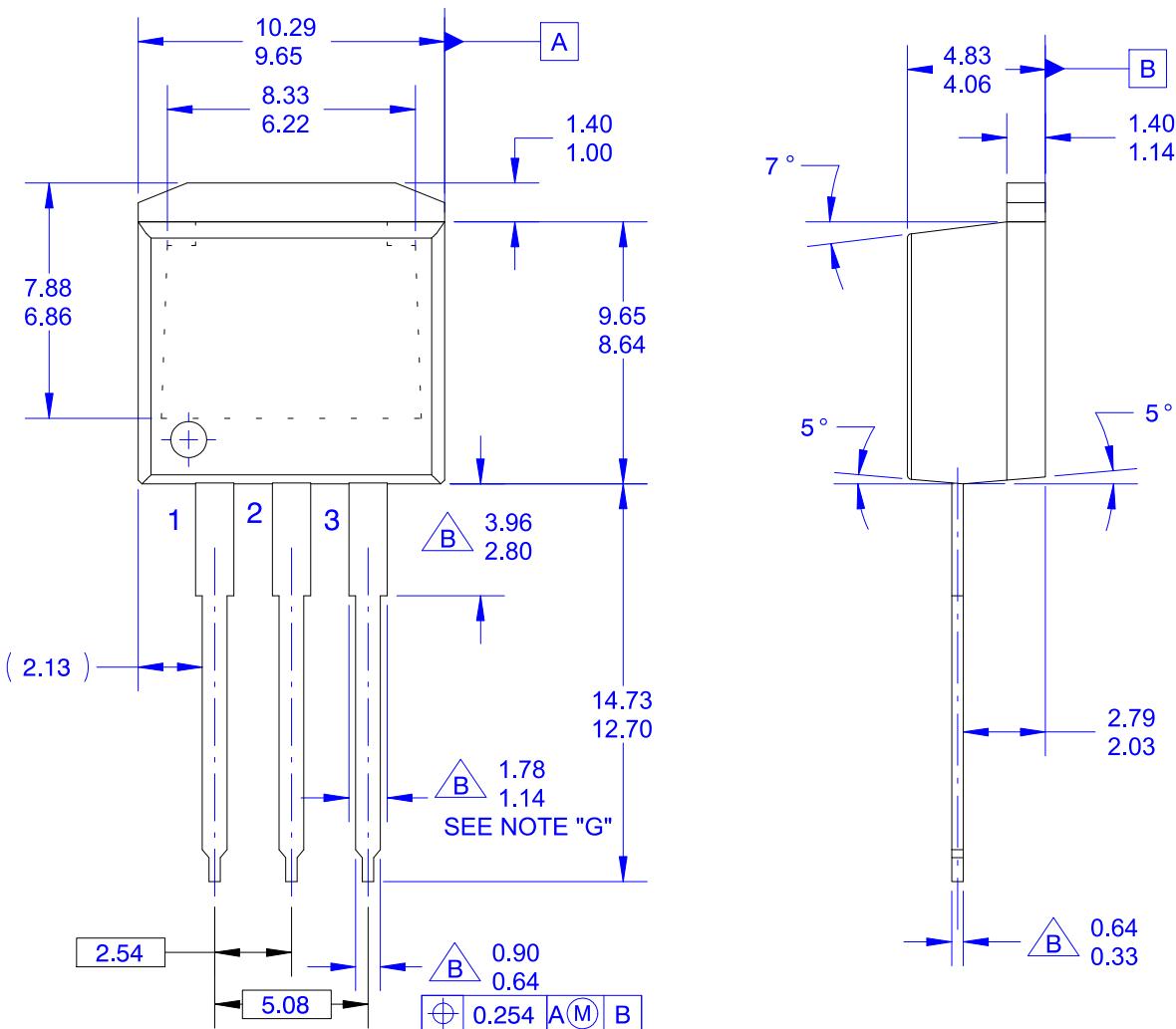
STYLE 12:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. NOT CONNECTED

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I2PAK (TO-262 3 LD)
CASE 418AV
ISSUE O

DATE 30 SEP 2016



NOTES:

- A. EXCEPT WHERE NOTED CONFORMS TO
TO262 JEDEC VARIATION AA.
- B** DOES NOT COMPLY JEDEC STD. VALUE.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DIMENSIONS ARE EXCLUSIVE OF BURRS,
MOLD FLASH AND TIE BAR PROTRUSIONS.
- E. DIMENSION AND TOLERANCE AS PER ANSI
Y14.5-1994.
- F. LOCATION OF PIN HOLE MAY VARY
(LOWER LEFT CORNER, LOWER CENTER
AND CENTER OF PACKAGE)
- G. MAXIMUM WIDTH FOR F102 DEVICE = 1.35 MAX.

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